

poly-SiGe を用いた CMOS IC 上の MEMS ジャイロ

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4.7 Processing of MEMS Gyroscopes on Top of CMOS ICs

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Exhibit #2: First poly-SiGe above-CMOS integrated gyroscope. The CMOS technology used is a standard 0.35 μm technology with 5 interconnect levels.

